

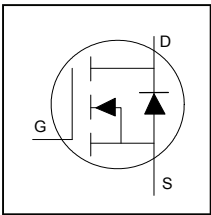
IR MOSFET - StrongIRFET™

Applications

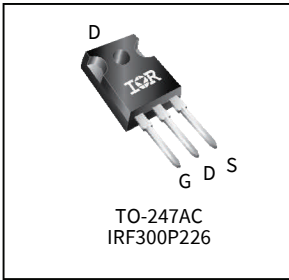
- UPS and Inverter applications
- Half-bridge and full-bridge topologies
- Resonant mode power supplies
- DC/DC and AC/DC converters
- OR-ing and redundant power switches
- Brushed and BLDC Motor drive applications
- Battery powered circuits

Benefits

- Improved Gate, Avalanche and Dynamic dv/dt Ruggedness
- Fully Characterized Capacitance and Avalanche SOA
- Enhanced body diode dv/dt and di/dt Capability
- Pb-Free ; RoHS Compliant ; Halogen-Free



V_{DSS}	300V
R_{DS(on)} typ. max	16mΩ
	19mΩ
I_D	100A



Halogen-Free



RoHS

G	D	S
Gate	Drain	Source

Base part number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
IRF300P226	TO-247AC	Tube	25	IRF300P226

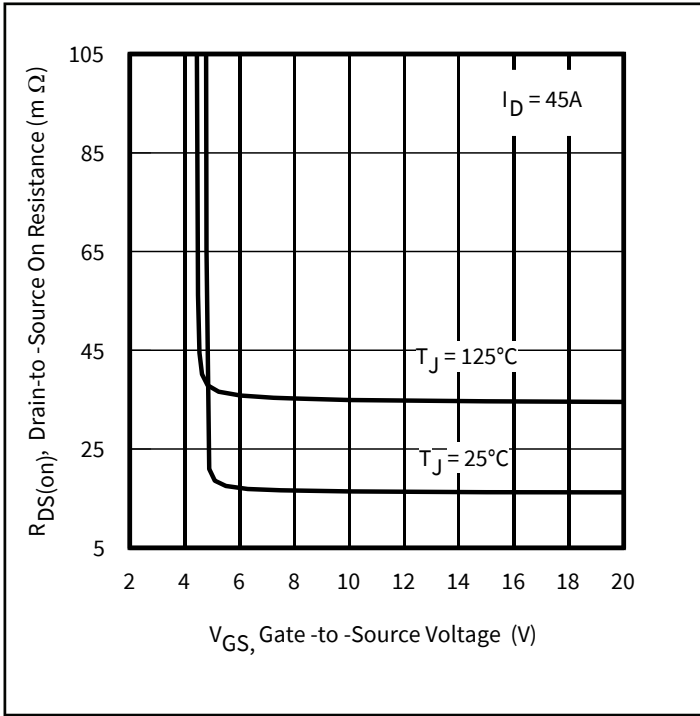


Figure 1 Typical On-Resistance vs. Gate Voltage

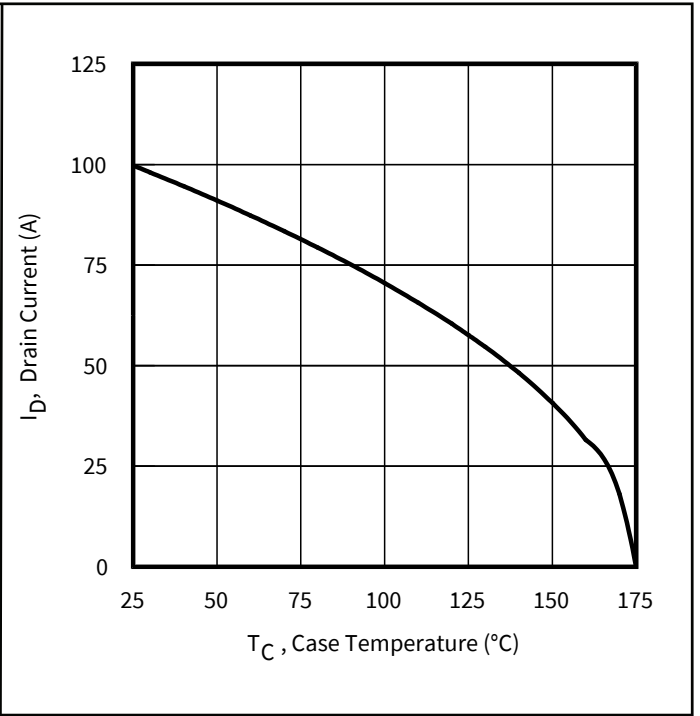


Figure 2 Maximum Drain Current vs. Case Temperature



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1 Parameters

Table1 Key performance parameters

Parameter	Values	Units
V_{DS}	300	V
$R_{DS(on) \max}$	19	m Ω
I_D	100	A

2 Maximum ratings and thermal characteristics

Table 2 Maximum ratings (at $T_J=25^\circ\text{C}$, unless otherwise specified)

Parameter	Symbol	Conditions	Values	Unit
Continuous Drain Current	I_D	$T_C = 25^\circ\text{C}$, $V_{GS} @ 10\text{V}$	100	A
Continuous Drain Current	I_D	$T_C = 100^\circ\text{C}$, $V_{GS} @ 10\text{V}$	71	
Pulsed Drain Current ①	I_{DM}	$T_C = 25^\circ\text{C}$	375	
Maximum Power Dissipation	P_D	$T_C = 25^\circ\text{C}$	556	W
Linear Derating Factor		$T_C = 25^\circ\text{C}$	3.7	W/ $^\circ\text{C}$
Peak Diode Recovery ③	dv/dt	$T_J = 175^\circ\text{C}$, $I_S = 22\text{A}$, $V_{DS} = 150\text{V}$	6.0	V/ns
Gate-to-Source Voltage	V_{GS}	-	± 20	V
Operating Junction and Storage Temperature Range	T_J T_{STG}	-	-55 to + 175	$^\circ\text{C}$
Soldering Temperature, for 10 seconds (1.6mm from case)	-	-	300	
Mounting Torque, 6-32 or M3 Screw	-	-	10 lbf·in (1.1 N·m)	-

Table 3 Thermal characteristics

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Junction-to-Case ⑦	$R_{\theta JC}$	T_J approximately 90°C	-	-	0.27	$^\circ\text{C}/\text{W}$
Case-to-Sink, Flat Greased Surface	$R_{\theta CS}$	-	-	0.24	-	
Junction-to-Ambient	$R_{\theta JA}$	-	-	-	40	

Table 4 Avalanche characteristics

Parameter	Symbol	Values	Unit
Single Pulse Avalanche Energy ②	E_{AS} (Thermally limited)	1559	mJ
Avalanche Current ①	I_{AR}	See Fig 16, 17, 23a, 23b	A
Repetitive Avalanche Energy ①	E_{AR}		mJ

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Limited by T_{Jmax} , starting $T_J = 25^\circ\text{C}$, $L = 7.8\text{mH}$, $R_G = 50\Omega$, $I_{AS} = 20\text{A}$, $V_{GS} = 10\text{V}$.
- ③ $I_{SD} \leq 22\text{A}$, $di/dt \leq 1000\text{A}/\mu\text{s}$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq 175^\circ\text{C}$.
- ④ Pulse width $\leq 400\mu\text{s}$; duty cycle $\leq 2\%$.
- ⑤ C_{oss} eff. (TR) is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .
- ⑥ C_{oss} eff. (ER) is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .
- ⑦ R_θ is measured at T_J approximately 90°C .

3 Electrical characteristics

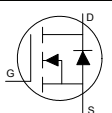
Table 5 Static characteristics

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 1mA$	300	-	-	V
Breakdown Voltage Temp. Coefficient	$\Delta V_{(BR)DSS} / \Delta T_J$	Reference to 25°C, $I_D = 2.5mA$ ①	-	0.12	-	V/°C
Static Drain-to-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 45A$	-	16	19	mΩ
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 270\mu A$	2.0	-	4.0	V
Drain-to-Source Leakage Current	I_{DSS}	$V_{DS} = 240V, V_{GS} = 0V$	-	-	10	μA
		$V_{DS} = 240V, V_{GS} = 0V, T_J = 125^\circ C$	-	-	300	
Gate-to-Source Forward Leakage	I_{GSS}	$V_{GS} = 20V$	-	-	200	nA
Gate Resistance	R_G		-	1.3	-	Ω

Table 6 Dynamic characteristics

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Forward Trans conductance	g_{fs}	$V_{DS} = 50V, I_D = 45A$	97	-	-	S
Total Gate Charge	Q_g	$I_D = 45A$ $V_{DS} = 150V$ $V_{GS} = 10V$	-	127	191	nC
Gate-to-Source Charge	Q_{gs}		-	44	-	
Gate-to-Drain Charge	Q_{gd}		-	24	-	
Total Gate Charge Sync. ($Q_g - Q_{gd}$)	Q_{sync}		-	103	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 150V$ $I_D = 45A$ $R_G = 2.7\Omega$ $V_{GS} = 10V$	-	25	-	ns
Rise Time	t_r		-	44	-	
Turn-Off Delay Time	$t_{d(off)}$		-	79	-	
Fall Time	t_f		-	32	-	
Input Capacitance	C_{iss}	$V_{GS} = 0V$ $V_{DS} = 50V$ $f = 1.0MHz$, See Fig.7	-	10030	-	pF
Output Capacitance	C_{oss}		-	863	-	
Reverse Transfer Capacitance	C_{rss}		-	3.8	-	
Effective Output Capacitance (Energy Related)	$C_{oss\ eff.(ER)}$	$V_{GS} = 0V, V_{DS} = 0V$ to 240V ⑥	-	552	-	
Output Capacitance (Time Related)	$C_{oss\ eff.(TR)}$	$V_{GS} = 0V, V_{DS} = 0V$ to 240V ⑤	-	961	-	

Table 7 Reverse Diode

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Continuous Source Current (Body Diode)	I_S	MOSFET symbol showing the integral reverse p-n junction diode. 	-	-	100	A
Pulsed Source Current (Body Diode) ①	I_{SM}		-	-	375	
Diode Forward Voltage	V_{SD}	$T_J = 25^\circ C, I_S = 45A, V_{GS} = 0V$ ④	-	-	1.2	V
Reverse Recovery Time	t_{rr}	$T_J = 25^\circ C$	-	156	-	ns
		$T_J = 125^\circ C$	-	215	-	
Reverse Recovery Charge	Q_{rr}	$T_J = 25^\circ C$	-	521	-	nC
		$T_J = 125^\circ C$	-	1145	-	
Reverse Recovery Current	I_{RRM}	$T_J = 25^\circ C$	-	5.0	-	A
		$T_J = 125^\circ C$	-	7.8	-	

4 Electrical characteristic diagrams

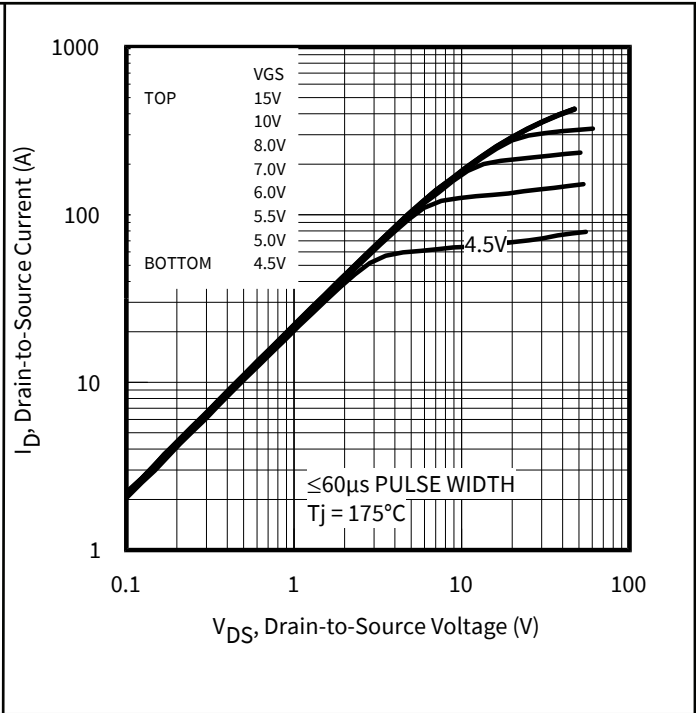
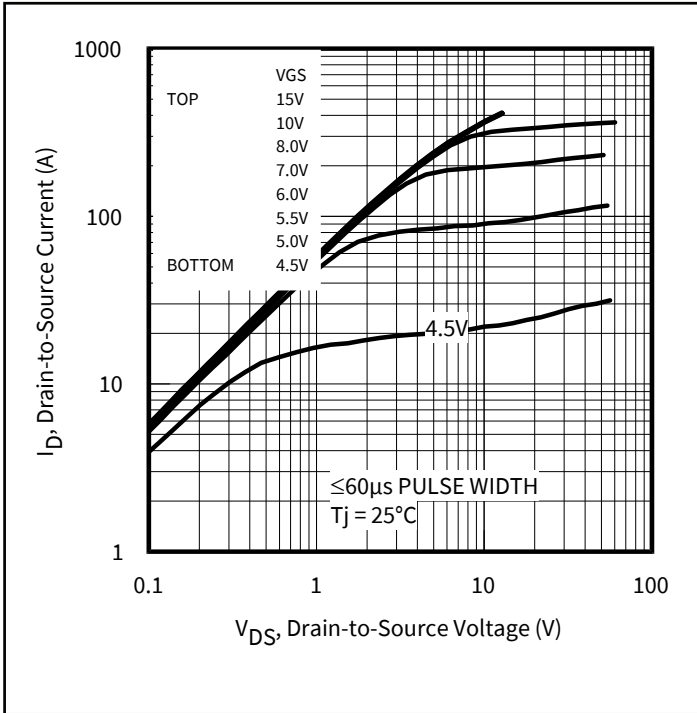


Figure 3 Typical Output Characteristics

Figure 4 Typical Output Characteristics

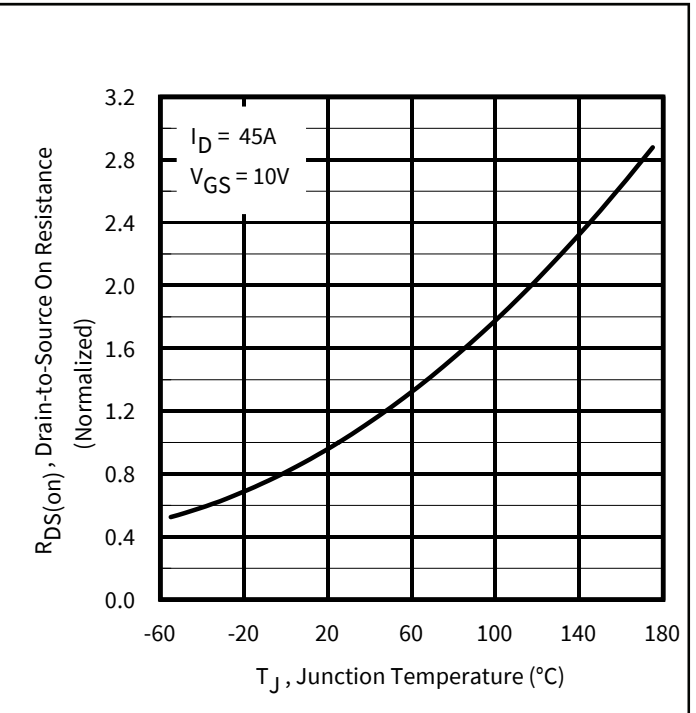
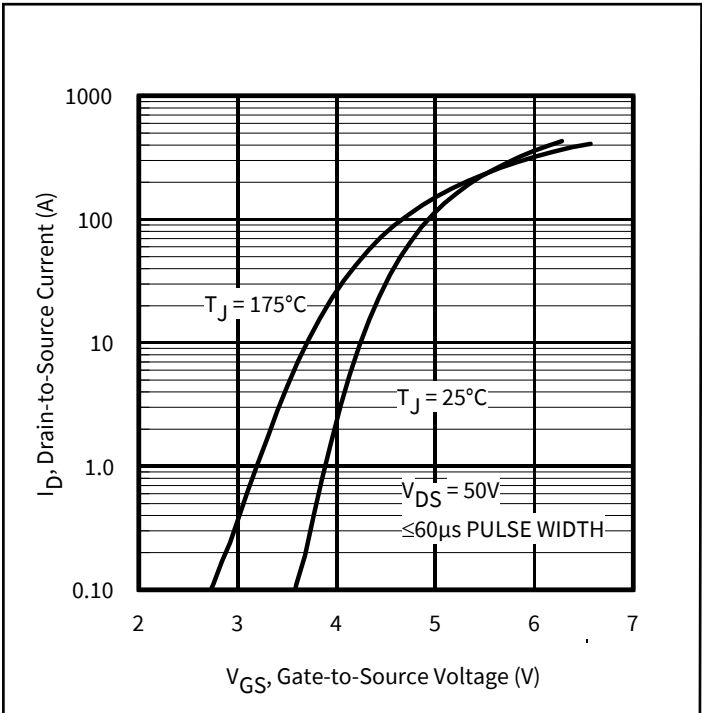


Figure 5 Typical Transfer Characteristics

Figure 6 Normalized On-Resistance vs. Temperature

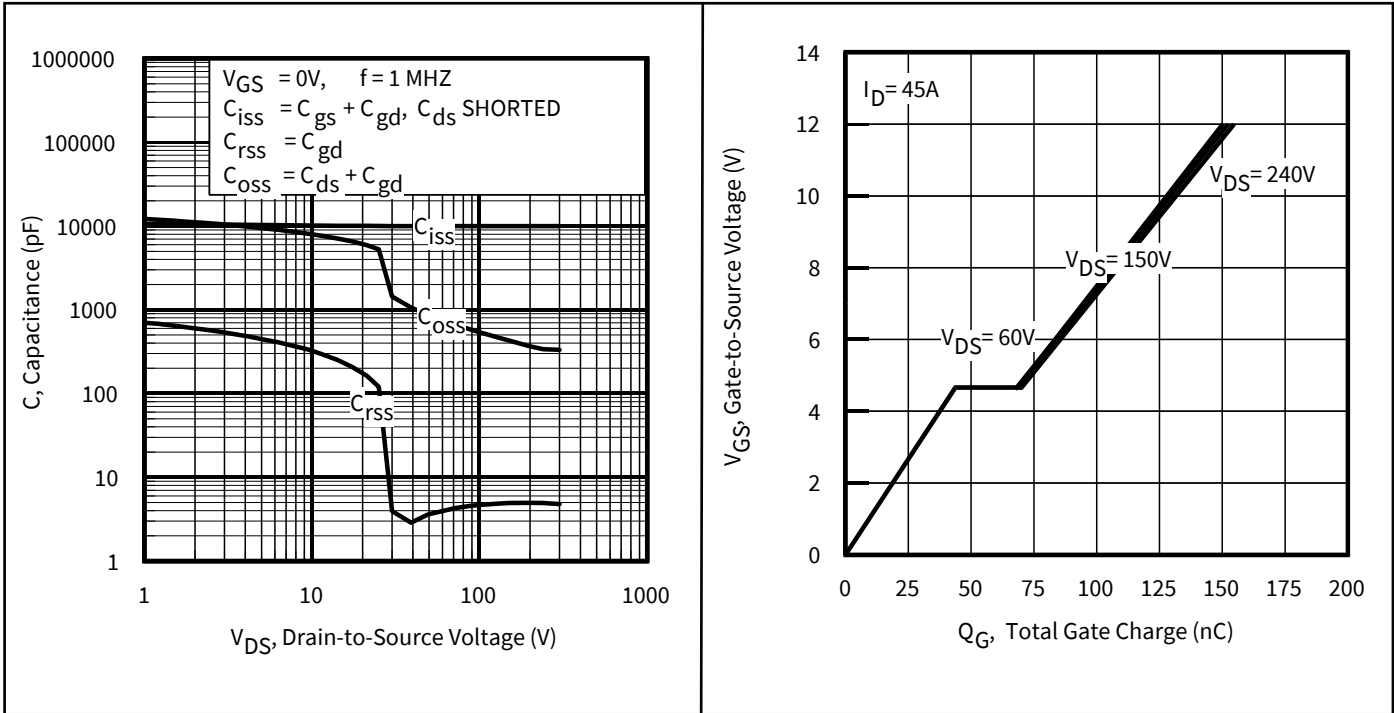


Figure 7 Typical Capacitance vs. Drain-to-Source Voltage

Figure 8 Typical Gate Charge vs. Gate-to-Source Voltage

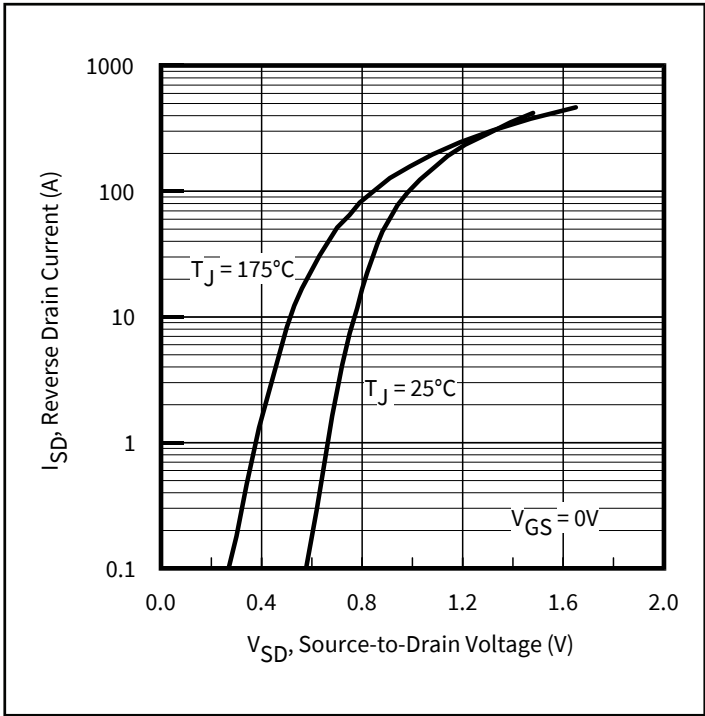


Figure 9 Typical Source-Drain Diode Forward Voltage

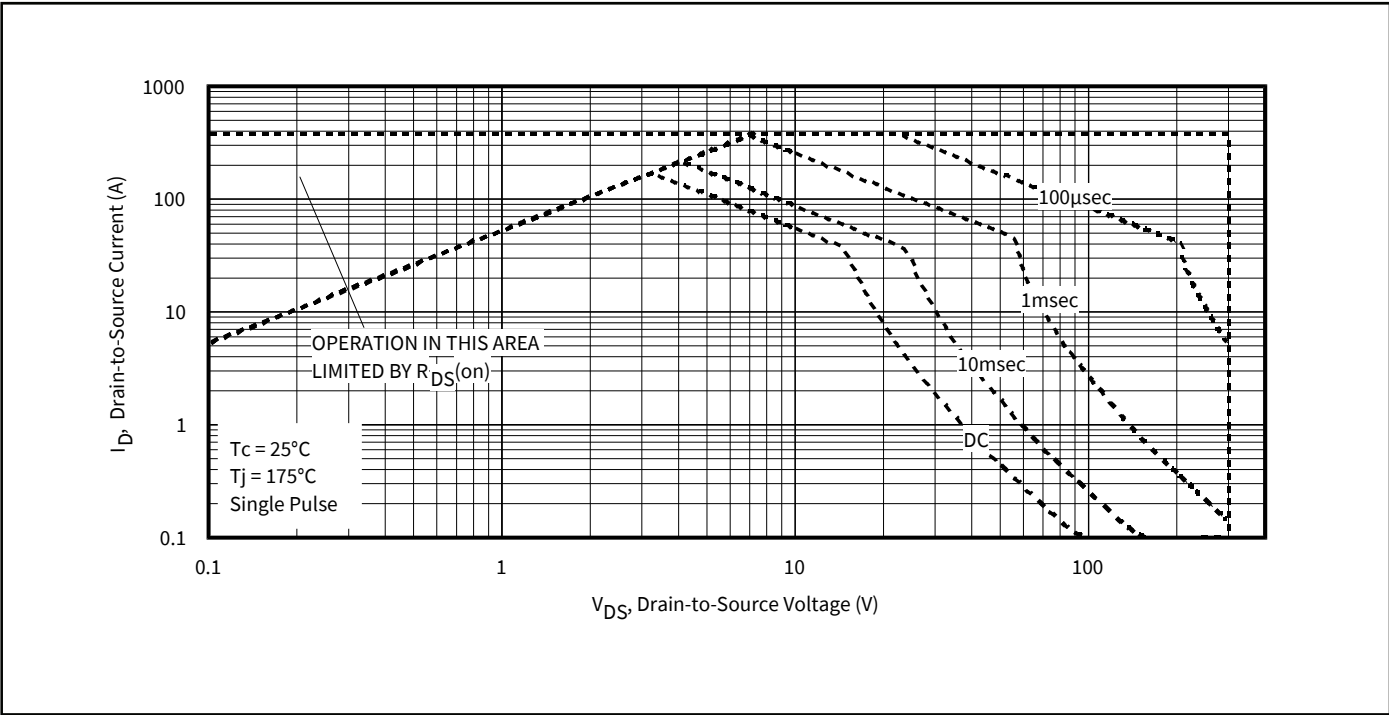


Figure 10 Maximum Safe Operating Area

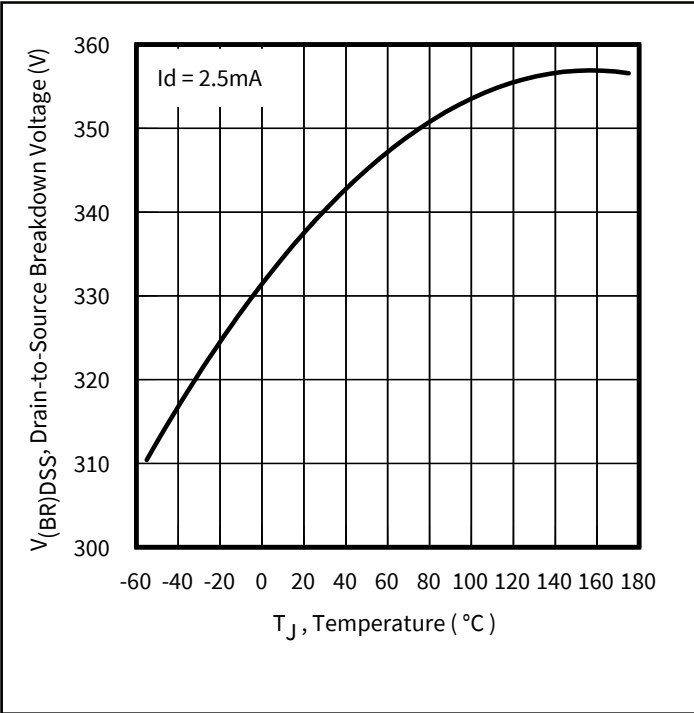


Figure 11 Drain-to-Source Breakdown Voltage

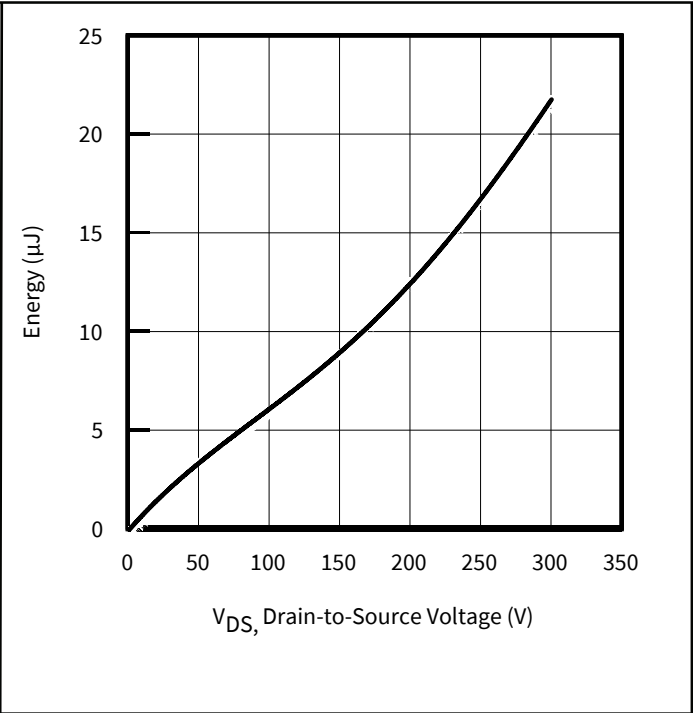


Figure 12 Typical Coss Stored Energy

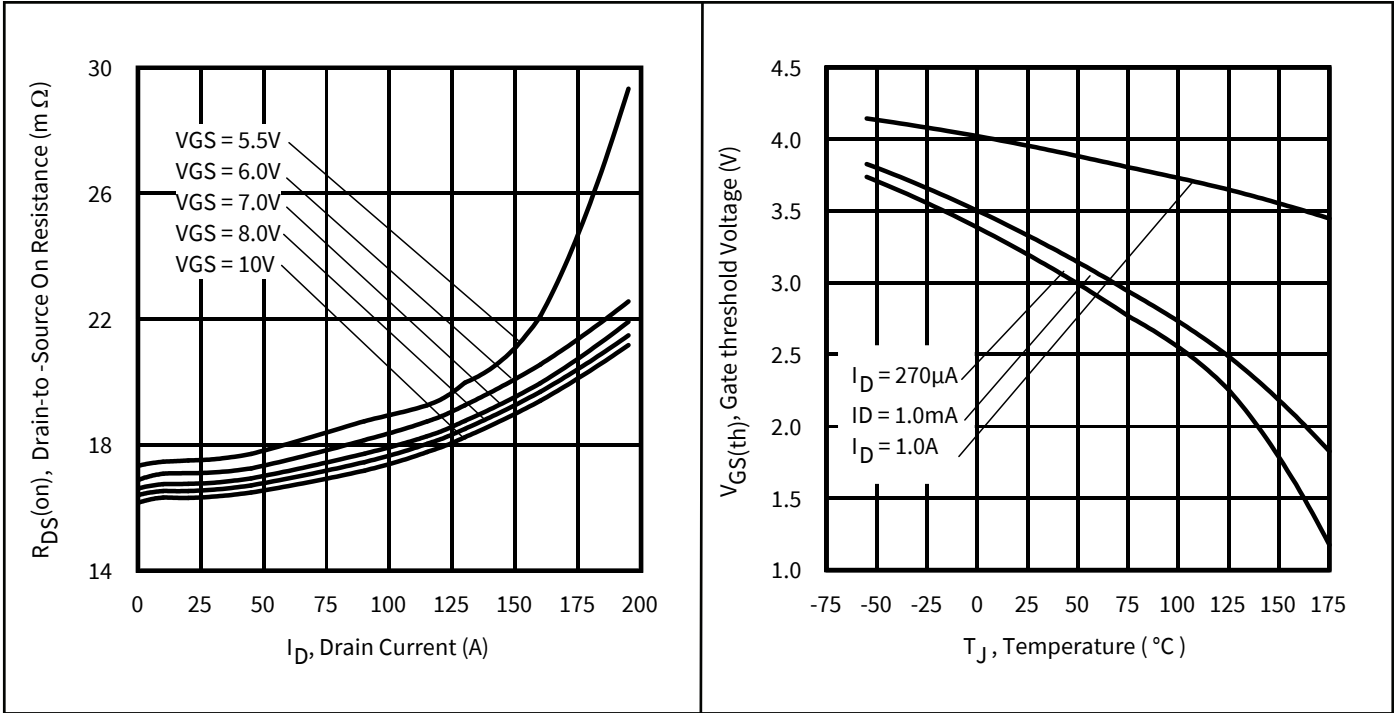


Figure 13 Typical On-Resistance vs. Drain Current

Figure 14 Threshold Voltage vs. Temperature

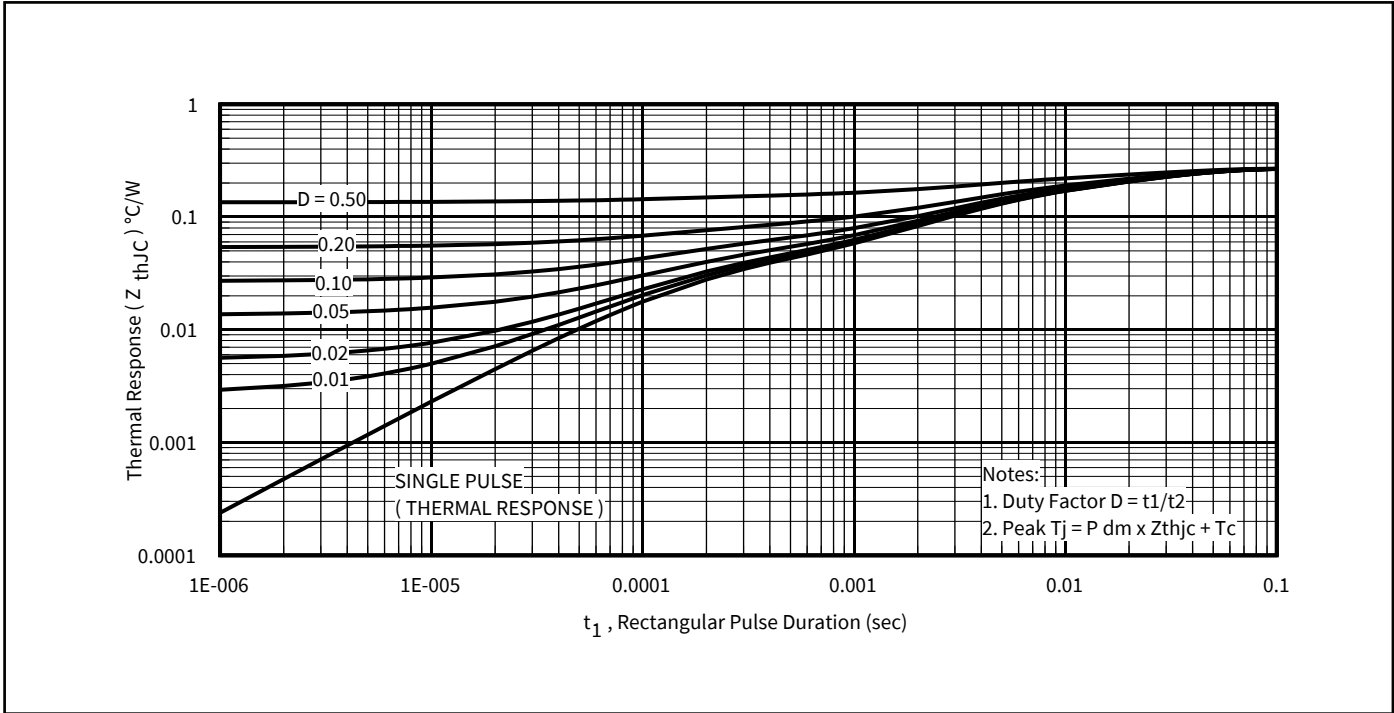


Figure 15 Maximum Effective Transient Thermal Impedance, Junction-to-Case

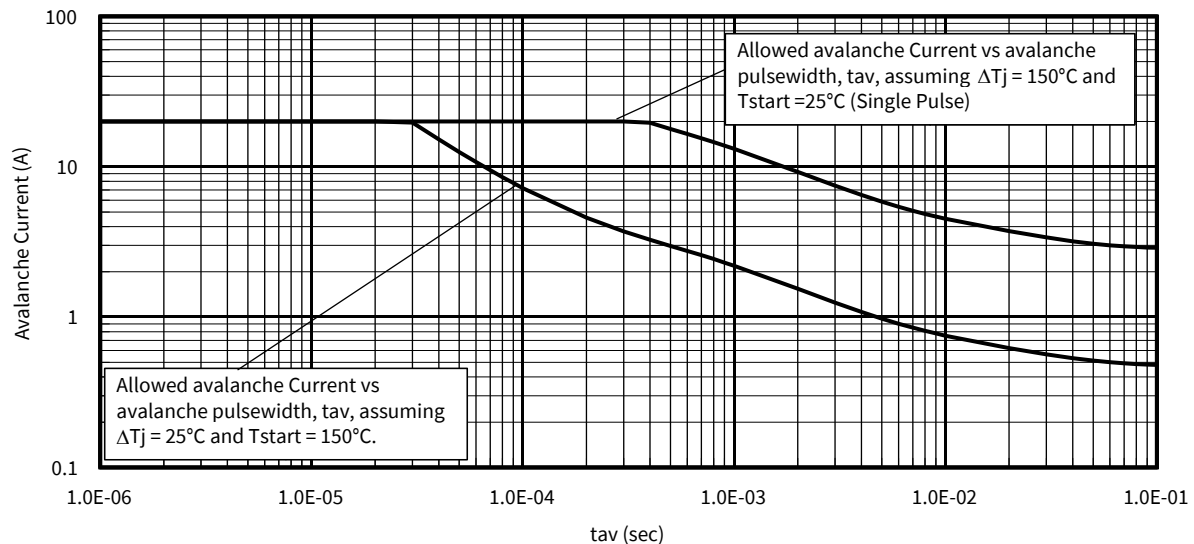
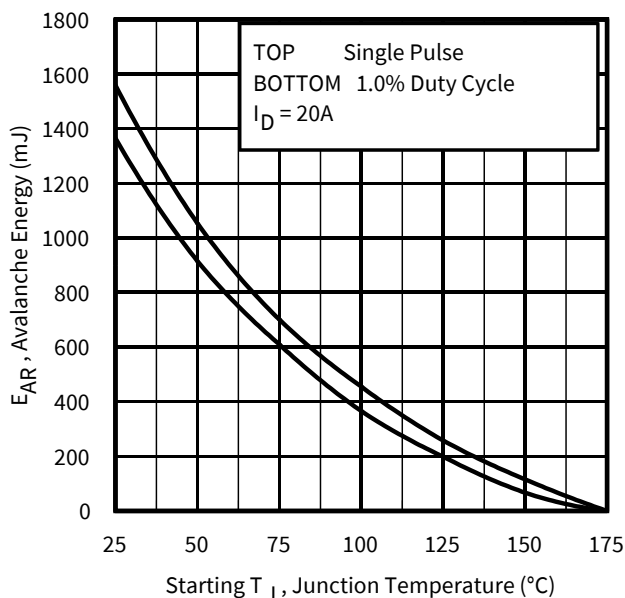


Figure 16 Avalanche Current vs. Pulse Width



Notes on Repetitive Avalanche Curves, Figures 16, 17:
(For further info, see AN-1005 at www.infineon.com)

1. Avalanche failures assumption:
Purely a thermal phenomenon and failure occurs at a temperature far in excess of $T_{j\text{max}}$. This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as $T_{j\text{max}}$ is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 23a, 23b.
4. $P_{D(\text{ave})}$ = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6. I_{av} = Allowable avalanche current.
7. ΔT = Allowable rise in junction temperature, not to exceed $T_{j\text{max}}$ (assumed as 25°C in Figure 15, 16).
 t_{av} = Average time in avalanche.
 D = Duty cycle in avalanche = $t_{av} \cdot f$
 $Z_{thJC}(D, t_{av})$ = Transient thermal resistance, see Figures 14)
 $P_{D(\text{ave})} = 1/2 (1.3 \cdot BV \cdot I_{av}) = \Delta T / Z_{thJC}$
 $I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{th}]$
 $E_{AS(AR)} = P_{D(\text{ave})} \cdot t_{av}$

Figure 17 Maximum Avalanche Energy vs. Temperature

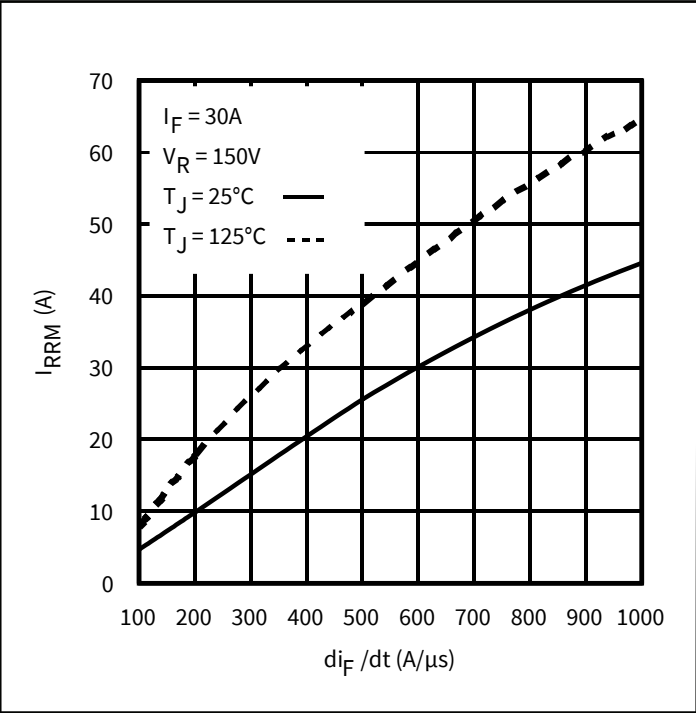


Figure 18 Typical Recovery Current vs. di_F/dt

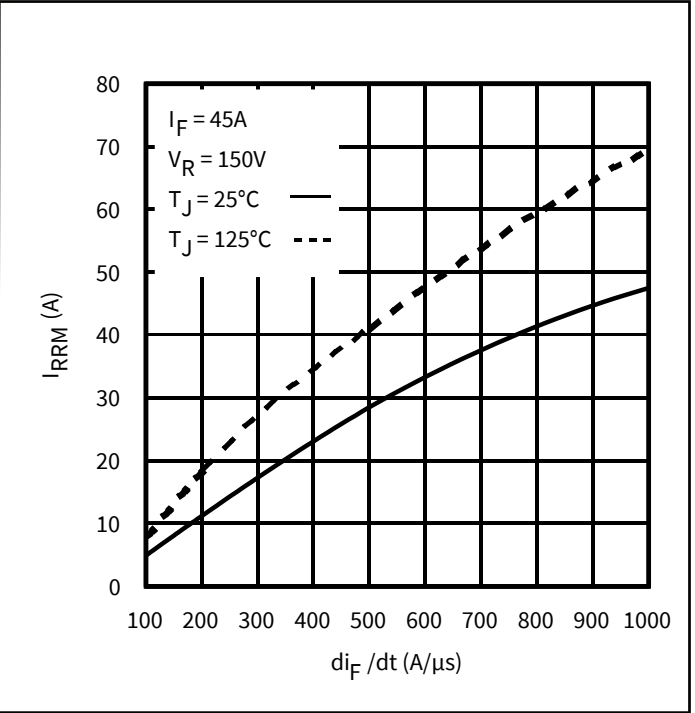


Figure 19 Typical Recovery Current vs. di_F/dt

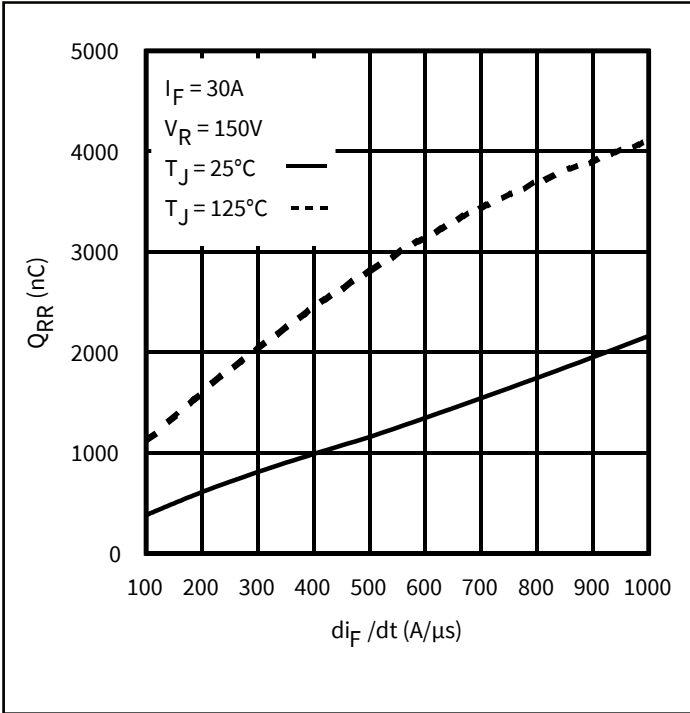


Figure 20 Typical Stored Charge vs. di_F/dt

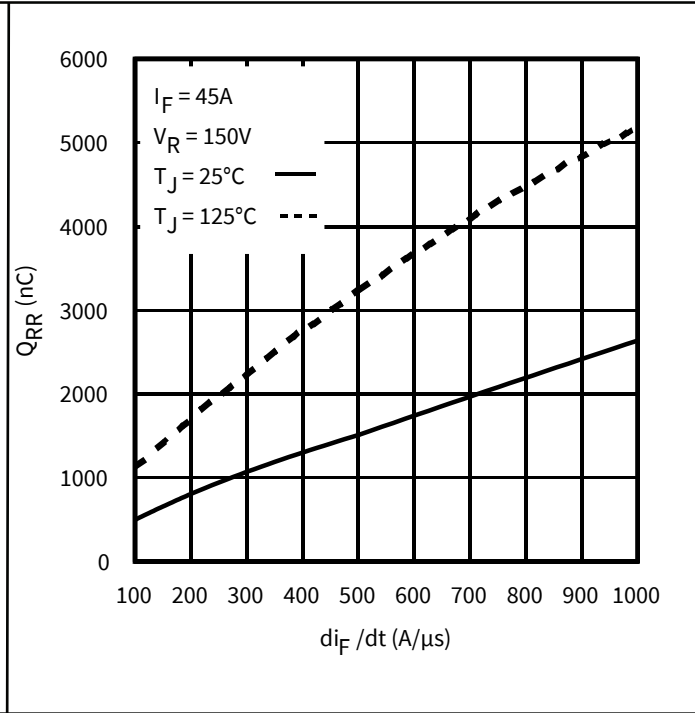


Figure 21 Typical Stored Charge vs. di_F/dt

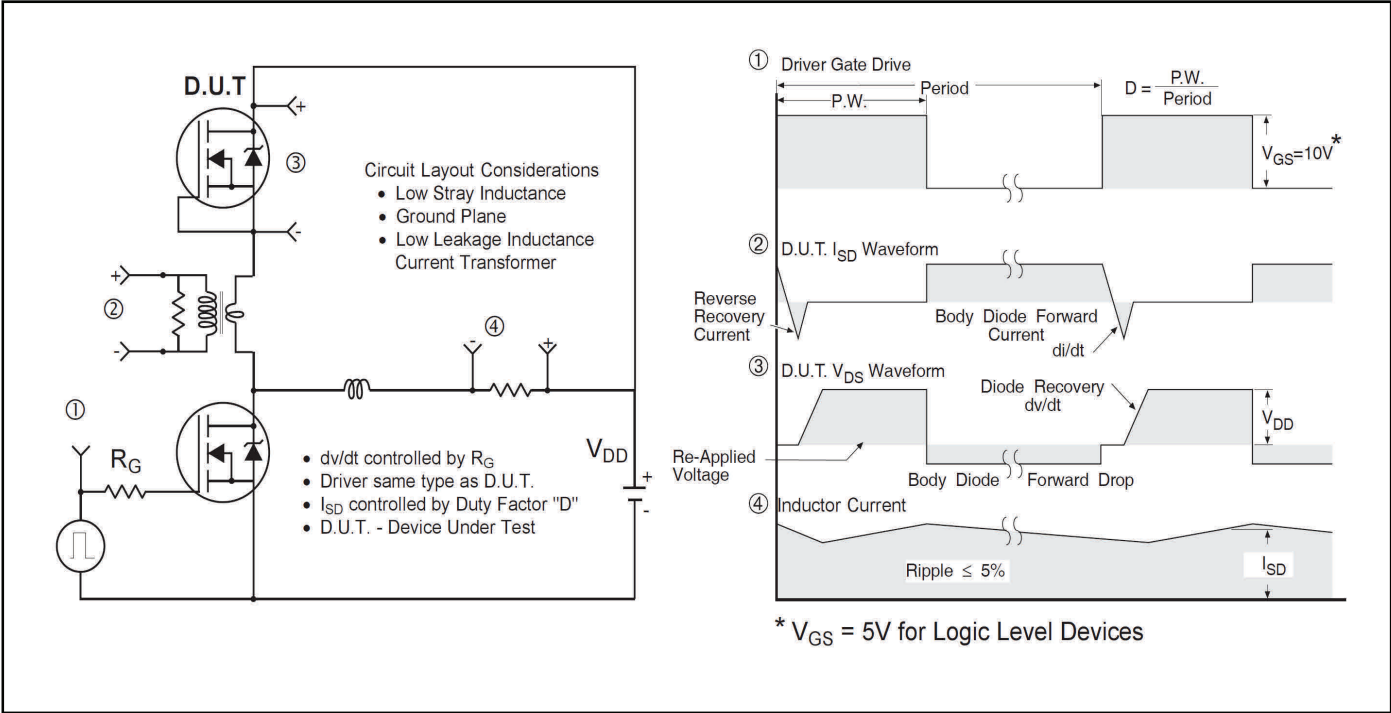


Figure 22 Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET™ Power MOSFETs

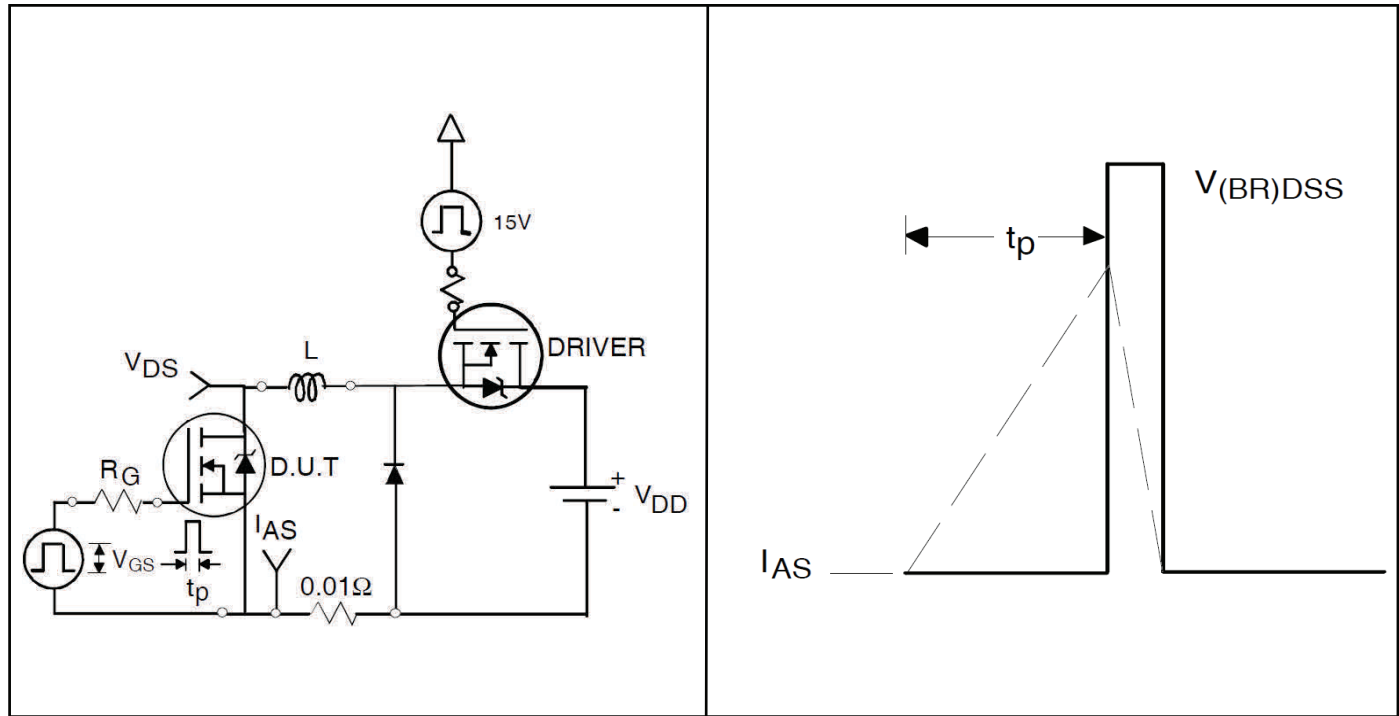


Figure 23a Unclamped Inductive Test Circuit

Figure 23b Unclamped Inductive Waveforms

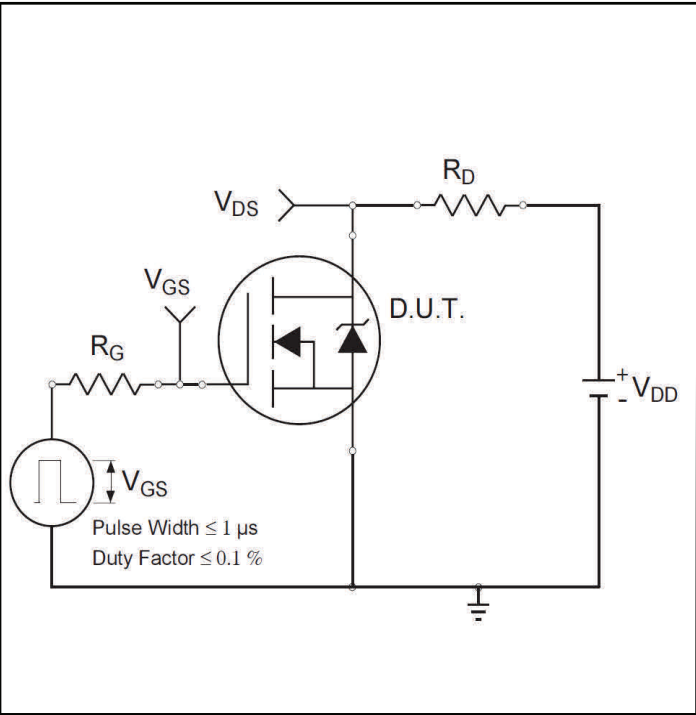


Figure 24a Switching Time Test Circuit

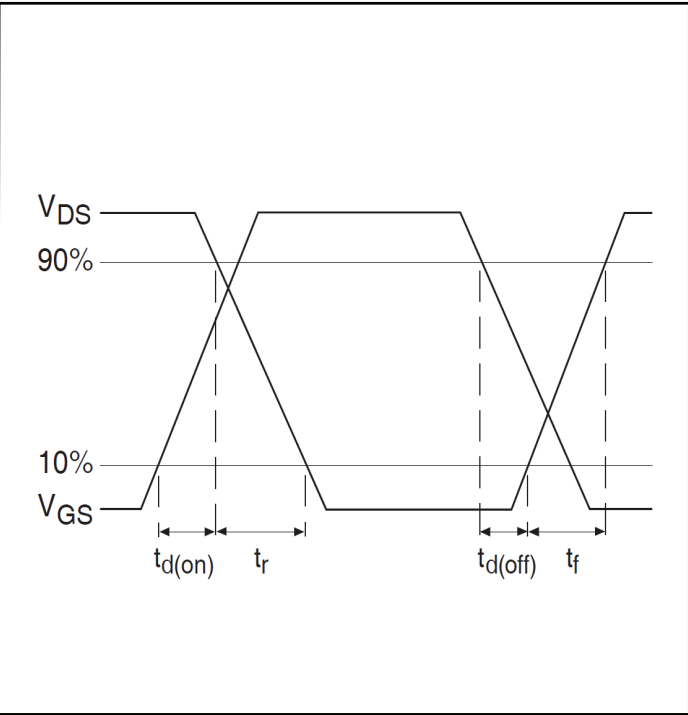


Figure 24b Switching Time Waveforms

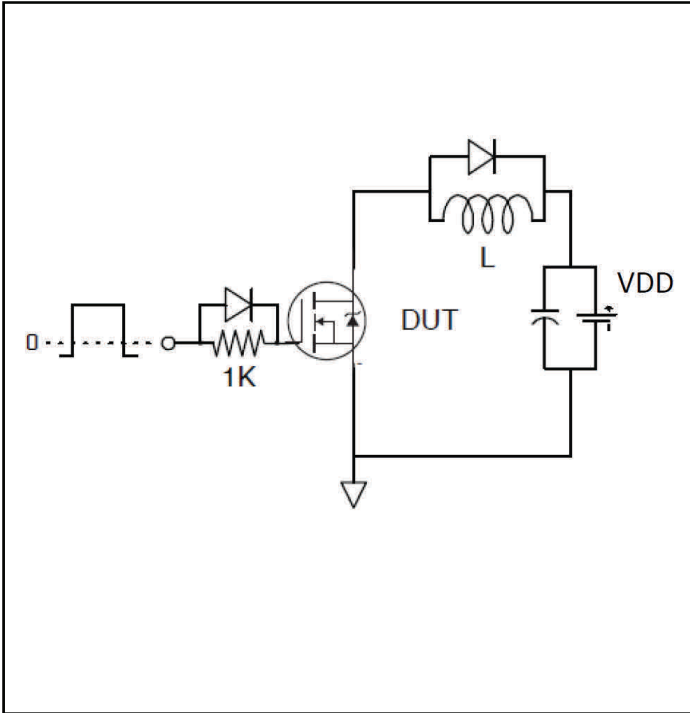


Figure 25a Gate Charge Test Circuit

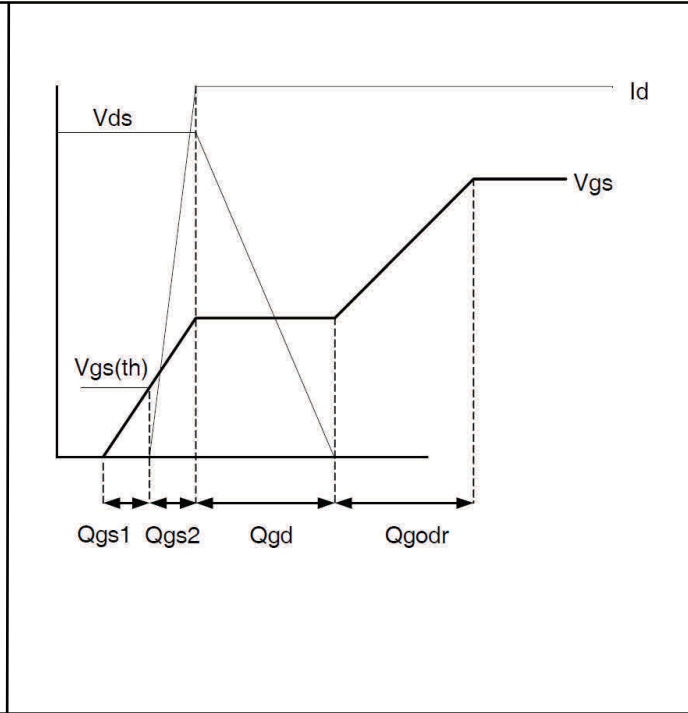


Figure 25b Gate Charge Waveform

6 Qualification Information

Qualification Information

Qualification Level	Industrial (per JEDEC JESD47F) †	
Moisture Sensitivity Level	TO-247AC	N/A
RoHS Compliant	Yes	

† Applicable version of JEDEC standard at the time of product release.

Revision History

Major changes since the last revision

Page or Reference	Revision	Date	Description of changes
All pages	2.0	2017-11-14	First release data sheet.
All pages	2.1	2018-08-09	- Datasheet updated with RTH from “0.48C/W” to “0.27C/W”-page 4 - Corrected fig 2,10,15,16,17 based on Rth change-page1, 8 & 9,10 - Corrected I_D / I_S from “75A” to “100A”-page1,3,4 - Corrected I_{DM} / I_{SM} from “300A” to “375A”, PD from “313W” to “556W”, Linear derating from “2.1W/C” to “3.7W/C” –page 3

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